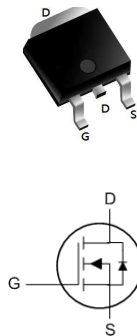


Applications

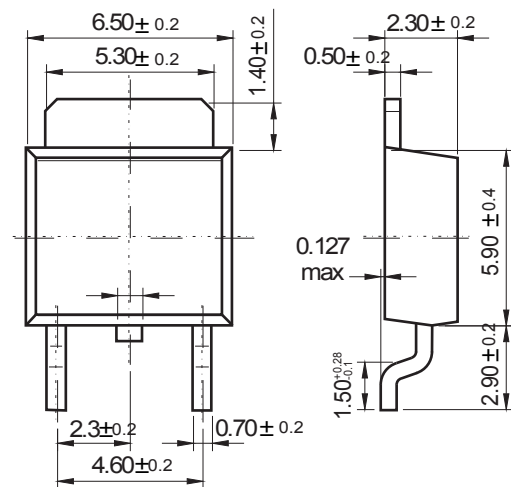
- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Motor Driving in Power Tool, E-vehicle, Robotics

Features

- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant



Unit: mm



Dimensions in inches and (millimeters)

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Pulsed Drain Current ⁽²⁾	I_{DM}	246	A
Avalanche Current ⁽³⁾	I_{AS}	42	A
Avalanche Energy ⁽³⁾	E_{AS}	88	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 100^\circ\text{C}$	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

100N10

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1.2	1.7	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		5.9	8.1	$\text{m}\Omega$
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5\text{V}$, $I_D = 15\text{A}$		7.8	12.0	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 20\text{A}$		82		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.71	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			104	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$		2360		pF
Output Capacitance	C_{oss}			368		pF
Reverse Transfer Capacitance	C_{rss}			5.9		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		1.7		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 75\text{V}$, $I_D = 20\text{A}$		34		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			16.8		nC
Gate Source Charge	Q_{gs}			5.4		nC
Gate Drain Charge	Q_{gd}			5.7		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 75\text{V}$ $R_L = 3.75\Omega$, $R_{GEN} = 6\Omega$		8.4		ns
Turn-On Rise Time	t_r			12.2		ns
Turn-Off DelayTime	$t_{D(off)}$			43		ns
Turn-Off Fall Time	t_f			18.9		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 15\text{A}$, $di_F/dt = 100\text{A}/\mu\text{s}$		49		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15\text{A}$, $di_F/dt = 100\text{A}/\mu\text{s}$		43		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	48	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.90	1.2	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\mu\text{H}$, $V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

RATING AND CHARACTERISTIC CURVES (100N10)

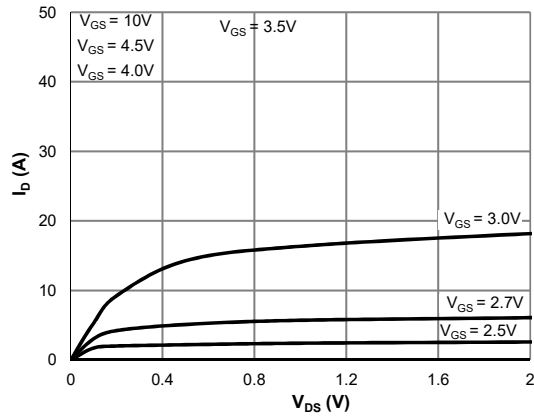


Figure 1: Saturation Characteristics

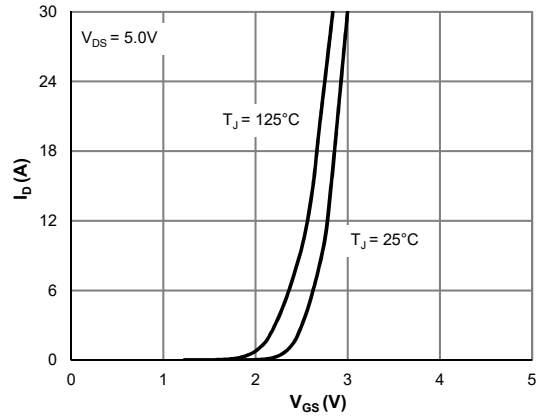


Figure 2: Transfer Characteristics

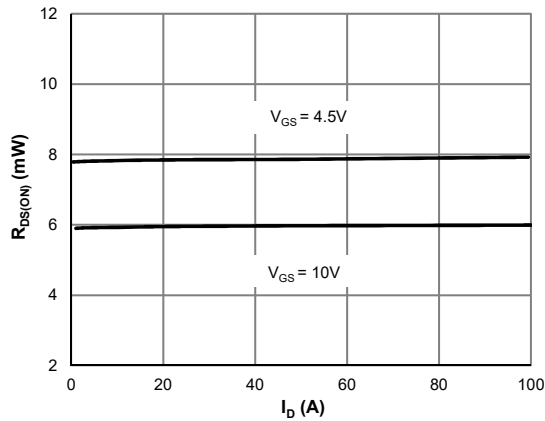


Figure 3: $R_{DS(ON)}$ vs. Drain Current

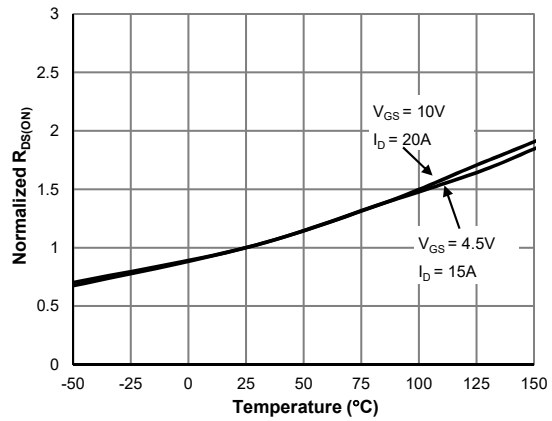


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

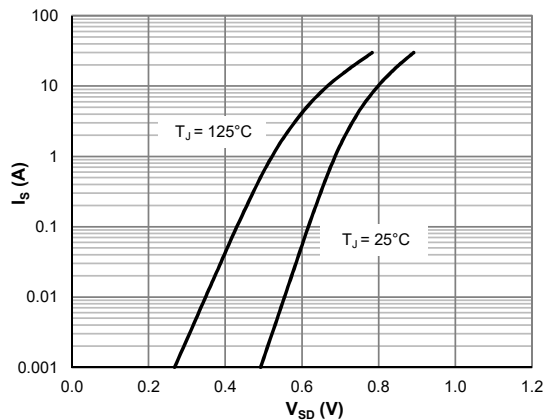


Figure 5: Body-Diode Characteristics

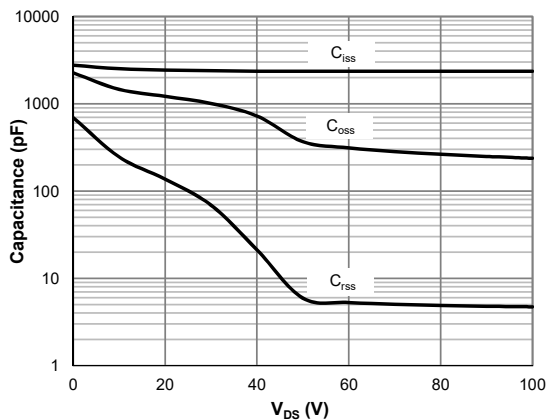


Figure 6: Capacitance Characteristics

RATING AND CHARACTERISTIC CURVES (100N10)

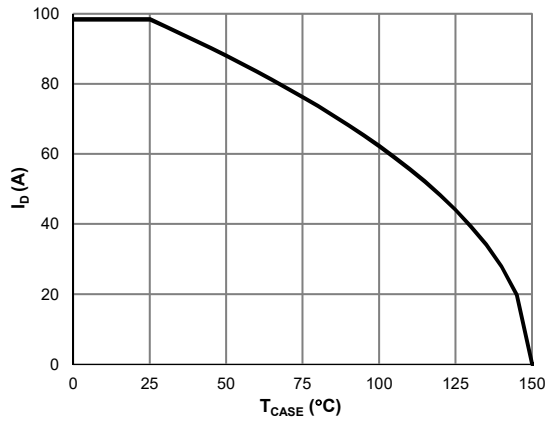


Figure 7: Current De-rating

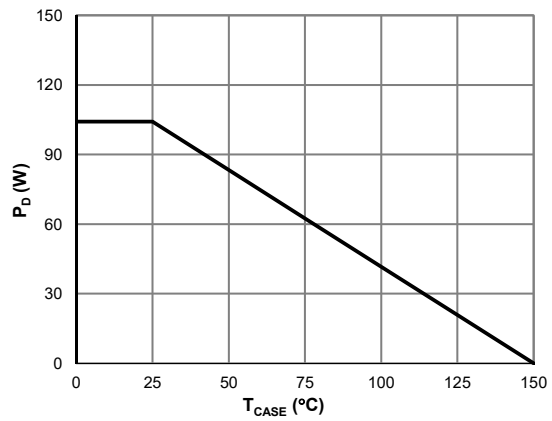


Figure 8: Power De-rating

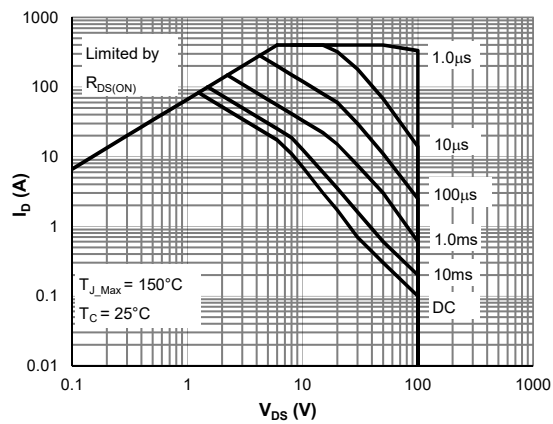


Figure 9: Maximum Safe Operating Area

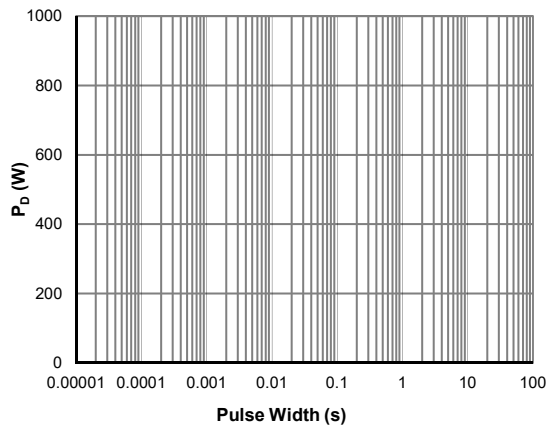


Figure 10: Single Pulse Power Rating, Junction-to-Case

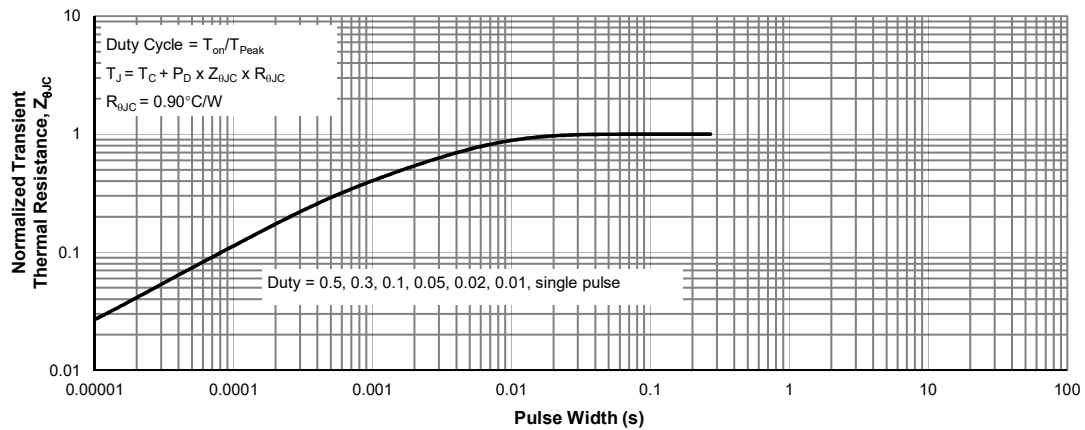


Figure 11: Normalized Maximum Transient Thermal Impedance